

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. F15320030239 US1	Application No. 10/707,690
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				Applicant Huiliang ZHU et al.	
				Filing Date 01/05/2004	Group 2818
U.S. PATENT DOCUMENTS					
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS SUBCLASS FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS					
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS SUBCLASS TRANSLATION YES NO
OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)					
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EXAMINER	<i>ShuLan</i>	DATE CONSIDERED 09/15/06			
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